

Description

The G16P03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

VDSS	RDS(ON) @-10V (typ)	ID
-30V	10 mΩ	-16A

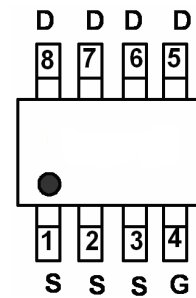
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

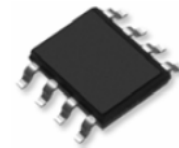
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOP-8 top view

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-16	A
Drain Current-Pulsed (Note 1)	I_{DM}	-48	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	41.67	$^\circ\text{C/W}$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol			Typ		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	-	10	15	mΩ
		V _{GS} =-4.5V, I _D =-7A	-	14	25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-10A	20	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	1750	-	PF
Output Capacitance	C _{OSS}		-	215	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	180	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-10A, V _{GS} =-10V, R _{GEN} =1Ω	-	9	-	nS
Turn-on Rise Time	t _r		-	8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	nC
Gate-Drain Charge	Q _{gd}		-	6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-2A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics



Figure 1: Switching Test Circuit

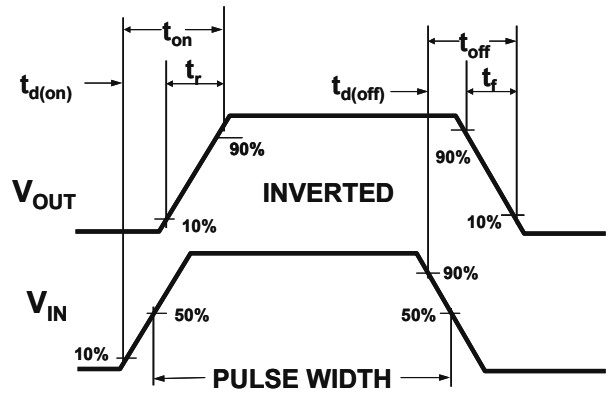


Figure 2: Switching Waveforms

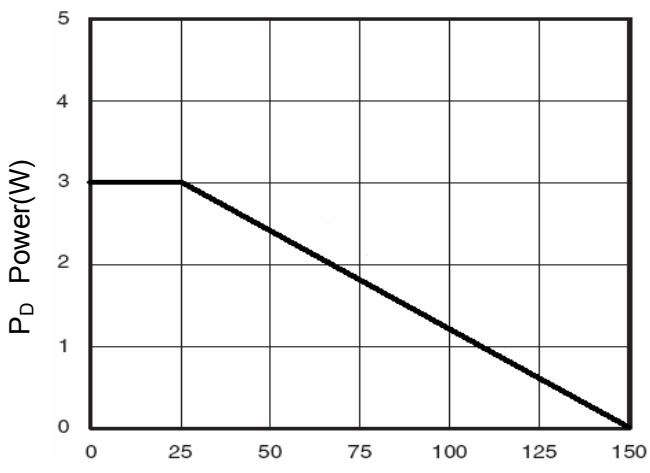


Figure 3 Power Dissipation

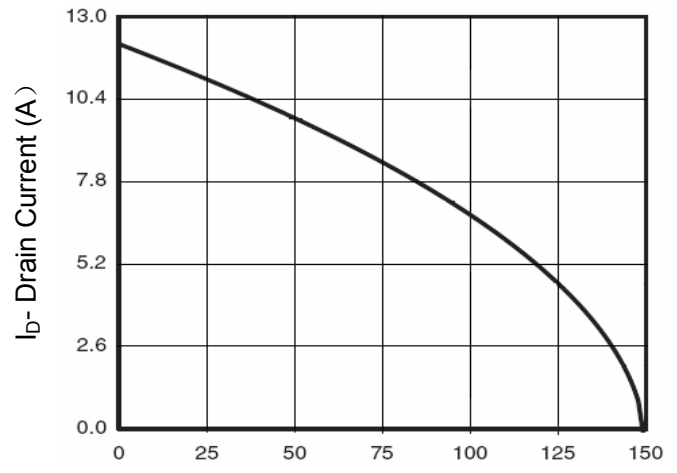


Figure 4 Drain Current

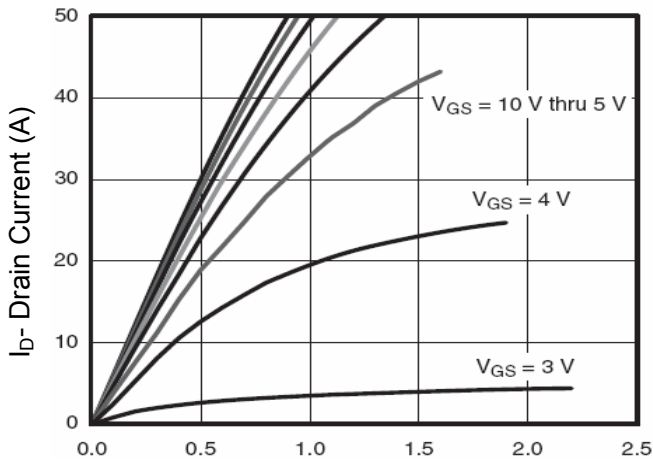


Figure 5 Output CHARACTERISTICS

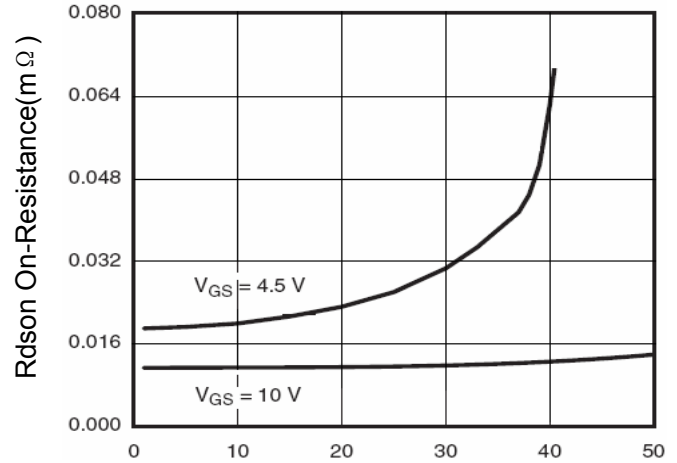
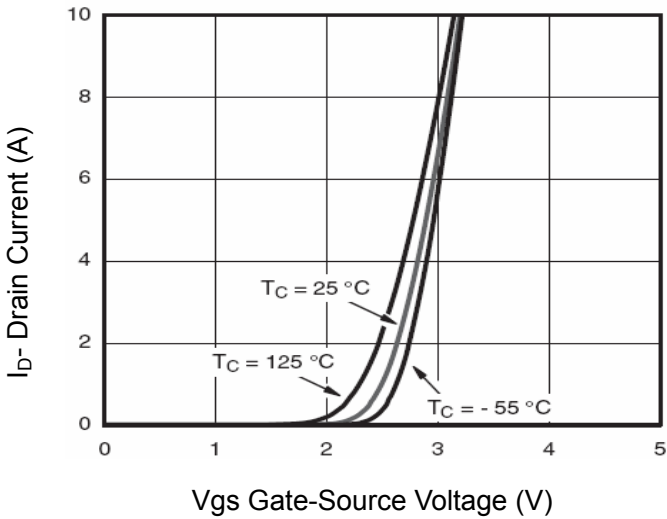
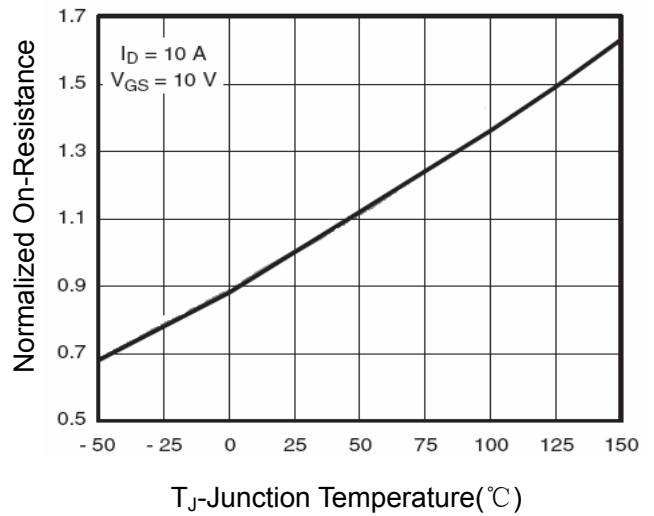


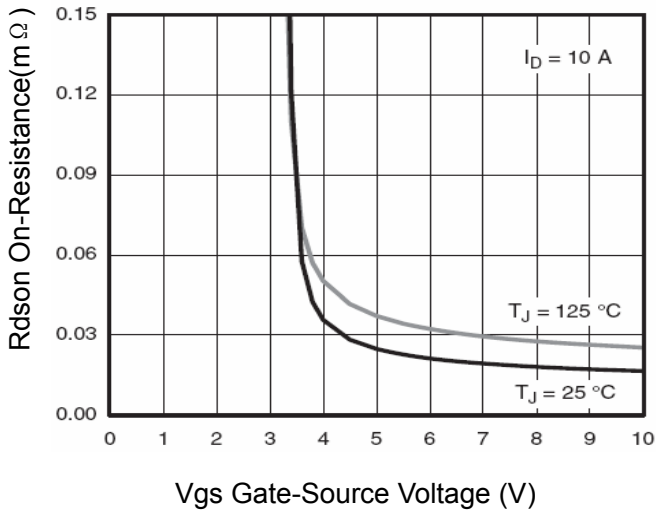
Figure 6 Drain-Source On-Resistance



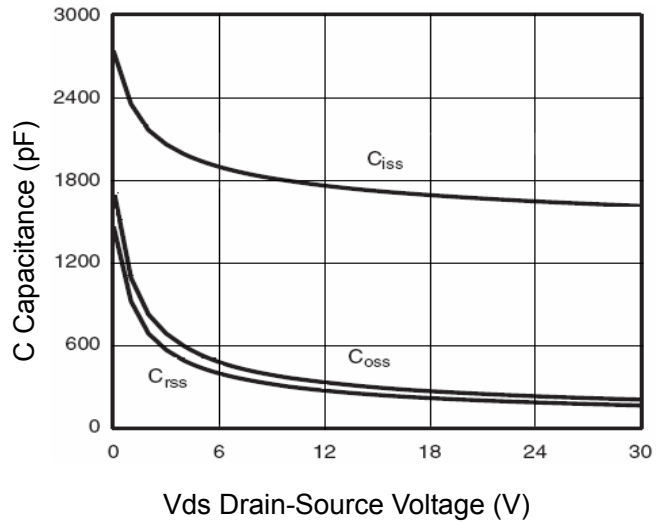
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



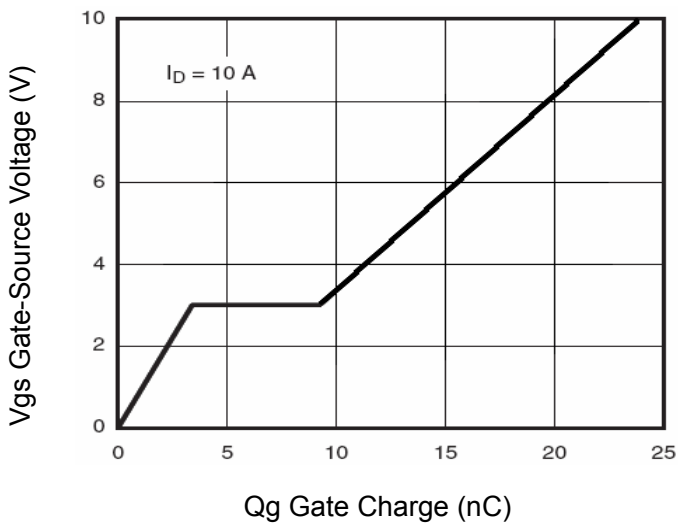
T_J -Junction Temperature($^\circ\text{C}$)
Figure 8 Drain-Source On-Resistance



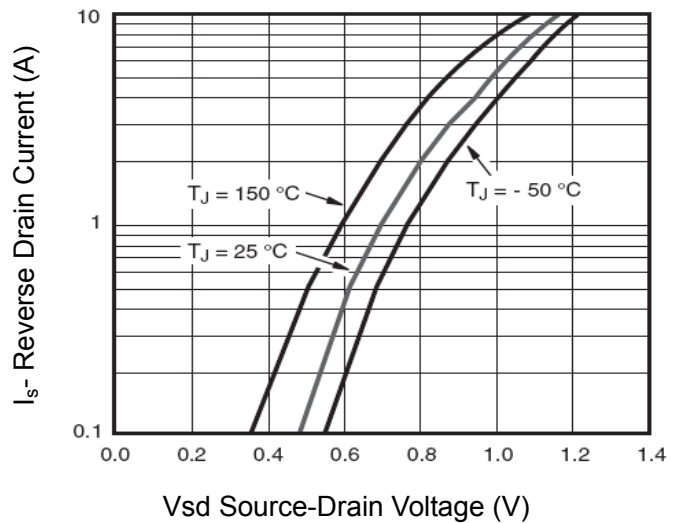
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

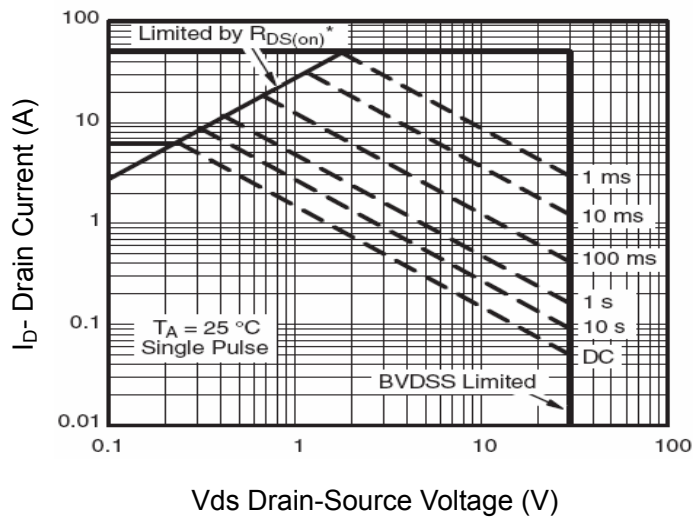


Figure 13 Safe Operation Area

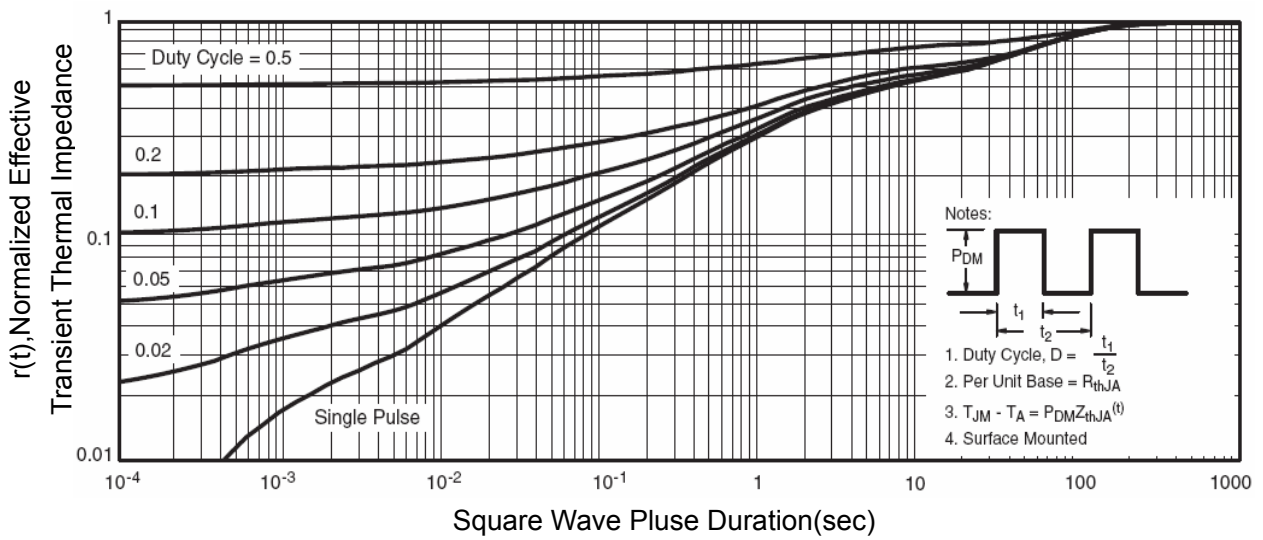


Figure 14 Normalized Maximum Transient Thermal Impedance